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Volume 34 Number 6 June 2013

SEMICONDUCTOR PHYSICS

062001 **The impact of germanium in strained Si/relaxed $Si_{1-x}Ge_x$ on carrier performance in non-degenerate and degenerate regimes** *(4 pages)*
EngSiew Kang, S Anwar, M T Ahmadi, and Razali Ismail

062002 **First principles study on the surface- and orientation-dependent electronic structure of a WO_3 nanowire** *(6 pages)*
Qin Yuxiang, Hua Deyan, and Li Xiao

062003 **The effect of InAs quantum-dot size and interdot distance on GaInP/GaAs/GaInAs/Ge multi-junction tandem solar cells** *(5 pages)*
Qu Xiaosheng, Zhang Sisi, Bao Hongyin, and Xiong Liling

SEMICONDUCTOR MATERIALS

063001 **Formation of single crystalline tellurium supersaturated silicon pn junctions by ion implantation followed by pulsed laser melting** *(5 pages)*
Wang Xiyuan, Huang Yongguang, Liu Dewei, Zhu Xiaoning, Cui Xiao, and Zhu Hongliang

063002 **Controlled growth of well-aligned ZnO nanowire arrays using the improved hydrothermal method** *(6 pages)*
Han Zhitao, Li Sisi, Chu Jinkui, and Chen Yong

063003 **The effects of cure temperature history on the stability of polyimide films** *(5 pages)*
Ning Wenguo, Li Heng, Zhu Chunsheng, Luo Le, Chen Dong, and Duan Zhenzhen

063004 **Development of aluminum-doped ZnO films for a-Si:H/μc-Si:H solar cell applications** *(6 pages)*
Lei Zhifang, Chen Guangyu, Gu Shibin, Dai Lingling, Yang Rong, Meng Yuan, Guo Ted, and Li Liwei

063005 **Numerical study of heat transport and fluid flow during the silicon crystal growth process by the Czochralski method** *(6 pages)*
Jin Chaohua

SEMICONDUCTOR DEVICES

064001 **Design and optimization of Ge profiles for improved thermal stability of SiGe HBTs** *(5 pages)*
Fu Qiang, Zhang Wanrong, Jin Dongyue, Ding Chunbao, Zhao Yanxiao, and Zhang Yujie

064002 **Field plated 0.15 μm GaN HEMTs for millimeter-wave application** *(5 pages)*
Ren Chunjiang, Li Zhonghui, Yu Xuming, Wang Quanhui, Wang Wen, Chen Tangsheng, and Zhang Bin

064003 **Planar InP-based Schottky barrier diodes for terahertz applications** *(4 pages)*
Zhou Jingtao, Yang Chengyue, Ge Ji, and Jin Zhi

064004 **Fabrication and characterization of an SOI MEMS gyroscope** *(5 pages)*
Zhong Weiwei, Han Guowei, Si Chaowei, Ning Jin, and Yang Fuhua

064005 **Fabrication and field emission characteristics of a novel planar-gate electron source with patterned carbon nanotubes for backlight units** *(5 pages)*
Zhang Yongai, Lin Tihang, Zeng Xiangyao, Zhou Xiongtu, and Guo Tailiang

064006 **An analytical model of the electric field distributions of buried superjunction devices** *(4 pages)*
Huang Haimeng and Chen Xingbi

(Continued on inside back cover)

064007 **A Verilog-A large signal model for InP DHBT including thermal effects** *(5 pages)*
Shi Yuxia, Jin Zhi, Pan Zhijian, Su Yongbo, Cao Yuxiong, and Wang Yan

064008 **A low temperature processed Si-quantum-dot poly-Si TFT nonvolatile memory device** *(4 pages)*
Sun Wei

064009 **Avalanche-enhanced photocurrents in pin silicon waveguides at 1550 nm wavelength** *(4 pages)*
Zhao Yong, Xu Chao, Jiang Xiaoqing, and Ge Huiliang

064010 **Accelerating the life of transistors** *(6 pages)*
Qi Haochun, Lü Changzhi, Zhang Xiaoling, and Xie Xuesong

SEMICONDUCTOR INTEGRATED CIRCUITS

065001 **A high-linearity InGaP/GaAs HBT power amplifier for IEEE 802.11a/n** *(6 pages)*
Cui Jie, Chen Lei, Kang Chunlei, Shi Jia, Zhang Xuguang, Ai Baoli, and Liu Yi

065002 **A wide range sigma–delta fractional-*N* frequency synthesizer with adaptive frequency calibration** *(5 pages)*
Wei Jianjun, Jiang Hanjun, Zhang Lingwei, Dong Jingjing, Li Fule, Wang Zhihua, and Zhang Chun

065003 **A wide load range, multi-mode synchronous buck DC–DC converter with a dynamic mode controller and adaptive slope compensation** *(8 pages)*
Zhang Chunhong, Yang Haigang, and Richard Shi

065004 **A 0.9-V switched-opamp-based delta–sigma ADC with dual cycle shift DWA** *(8 pages)*
Zhao Jinchen, Zhao Menglian, Wu Xiaobo, and Wang Hanqing

065005 **A low power time-interleaved 10-bit 250-MSPS charge domain pipelined ADC for IF sampling** *(8 pages)*
Chen Zhenhai, Qian Hongwen, Huang Songren, Zhang Hong, and Yu Zongguang

065006 **An I/Q DAC with gain matching circuit for a wireless transmitter** *(6 pages)*
Tang Hualian, Zhuang Yiqi, Jing Xin, and Zhang Li

065007 **Delay-area trade-off for MPRM circuits based on hybrid discrete particle swarm optimization** *(6 pages)*
Jiang Zhidi, Wang Zhenhai, and Wang Pengjun

065008 **A noise immunity improved level shift structure for a 600 V HVIC** *(5 pages)*
Zhang Yunwu, Zhu Jing, Sun Guodong, Liu Cuichun, Sun Weifeng, and Qian Qinsong

065009 **A continuously and widely tunable analog baseband chain with digital-assisted calibration for multi-standard DBS applications** *(9 pages)*
Li Songting, Li Jiancheng, Gu Xiaochen, and Wang Hongyi

065010 **A multiple transistor combination low-voltage curvature-corrected bandgap reference** *(5 pages)*
Su Kai, Gong Min, Qin Huaibin, and Sun Chen

SEMICONDUCTOR TECHNOLOGY

066001 **Interconnects for nanoscale MOSFET technology: a review** *(8 pages)*
Amit Chaudhry

066002 **Structure design and film process optimization for metal-gate stress in 20 nm nMOS devices** *(5 pages)*
Fu Zuozhen, Yin Huaxiang, Ma Xiaolong, Chai Shumin, Gao Jianfeng, and Chen Dapeng

066003 **Prevention of plasma-induced damage on thin gate oxides in BEOL sub-half micron CMOS processing** *(4 pages)*
He Qi, Zhao Wenbin, Peng Li, and Yu Zongguang

066004 **Two-dimensional simulation of inductively coupled plasma based on COMSOL and comparison with experimental data** *(7 pages)*
Cheng Jia, Ji Linhong, Wang Kesheng, Han Chuankun, and Shi Yixiang

066005 **Effective interface passivation of a Ge/HfO_2 gate stack using ozone pre-gate treatment and ozone ambient annealing** *(4 pages)*
Zhao Mei, Liang Renrong, Wang Jing, and Xu Jun